

UNISONIC TECHNOLOGIES CO., LTD

12N06Z **Power MOSFET**

12A, 60V N-CHANNEL POWER MOSFET

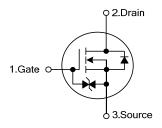
DESCRIPTION

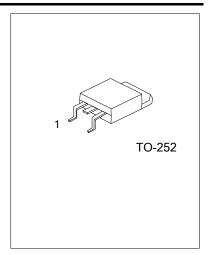
The UTC 12N06Z is an N-channel enhancement mode Power MOSFET using UTC's advanced technology to provide customers with a minimum on-state resistance, high switching speed and low gate charge.

FEATURES

- * 12A, 60V, $R_{DS(on)}$ < 0.10 Ω @ V_{GS} = 10V
- * High switching speed
- * Low gate charge
- * Halogen Free

SYMBOL

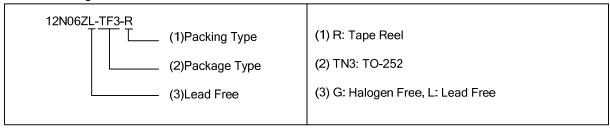




ORDERING INFORMATION

Ordering Number		Dookogo	Pin Assignment			Dooking	
Lead Free	Halogen Free	Package	1	2	3	Packing	
12N06ZL-TN3-R	12N06ZG-TN3-R	TO-252	G	D	S	Tape Reel	

Note: Pin Assignment: G: Gate D: Drain S: Source



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ABSOLUTE MAXIMUM RATINGS

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		$V_{ extsf{DSS}}$	60	V
Gate-Source Voltage		V_{GSS}	±20	V
Drain Current	Continuous $T_C = 25^{\circ}C$	l _D	12	Α
	Pulsed	I _{DM}	48	Α
Total Dissipation at T _C = 25°C		P _{TOT}	30	W
Peak Diode Recovery dv/dt		dv/dt	15	V/ns
Avalanche Energy		E _{AS}	140	mJ
Junction Temperature		TJ	-55~+175	°C
Storage Temperature Range		T _{STG}	-55~+175	°C

Notes: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL CHARACTERISTICS

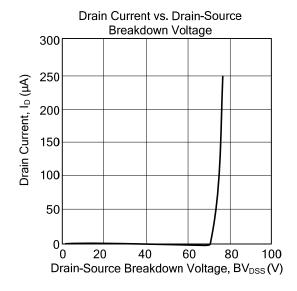
PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient Max	θ_{JA}	100	°C/W
Junction to Case Max	θ_{JC}	5	°C/W

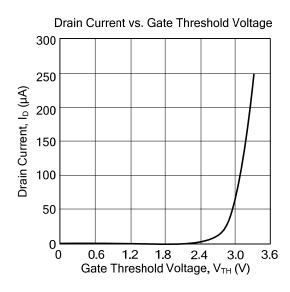
■ ELECTRICAL CHARACTERISTICS (T_{CASE}=25°C, unless otherwise specified)

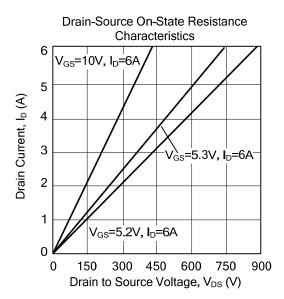
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT		
OFF CHARACTERISTICS								
Drain-Source Breakdown Voltage	BV _{DSS}	I _D =250 μ A	60			V		
Drain-Source Leakage Current	I _{DSS}	V _{DS} =60V			1	μΑ		
Gate- Source Leakage Current Forward	I_{GSS}	V _{GS} =±20V			±10	μΑ		
ON CHARACTERISTICS								
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=V_{GS}$, $I_D=250\mu A$	1		3	V		
Static Drain-Source On-State Resistance	R _{DS(ON)}	V_{DS} =10V, I_{D} =6A		0.08	0.1	Ω		
On State Drain Current	$I_{D(ON)}$	V _{GS} =10V, V _{DS} =1V	5		30	Α		
DYNAMIC PARAMETERS								
Input Capacitance	C_{ISS}			350		pF		
Output Capacitance	Coss	V _{DS} =25V, f=1MHz, V _{GS} =0V		75		pF		
Reverse Transfer Capacitance	C_{RSS}			30		pF		
SWITCHING PARAMETERS								
Total Gate Charge	Q_G			7.5	10	nC		
Gate to Source Charge	Q_GS	V_{GS} =5V, I_D =12A, V_{DD} =48V		2.5		nC		
Gate to Drain Charge	Q_GD			3.0		nC		
Turn-ON Delay Time	$t_{D(ON)}$			10		ns		
Rise Time	t _R	V_{DD} =30V, I_{D} =6A, R_{G} =4.7 Ω ,		35		ns		
Turn-OFF Delay Time	t _{D(OFF)}	_V _{GS} =0~10V		20		ns		
Fall-Time	t _F			13		ns		
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS								
Maximum Body-Diode Continuous Current	Is				12	Α		
Maximum Body-Diode Pulsed Current	I _{SM}				48	Α		
Drain-Source Diode Forward Voltage	V_{SD}	I _S =12A			1.5	V		

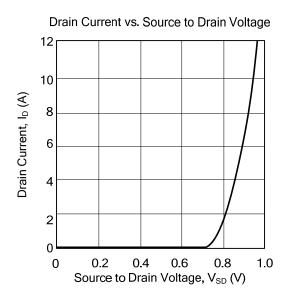
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■ TYPICAL CHARACTERISTICS









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